

# TPCA8068-H

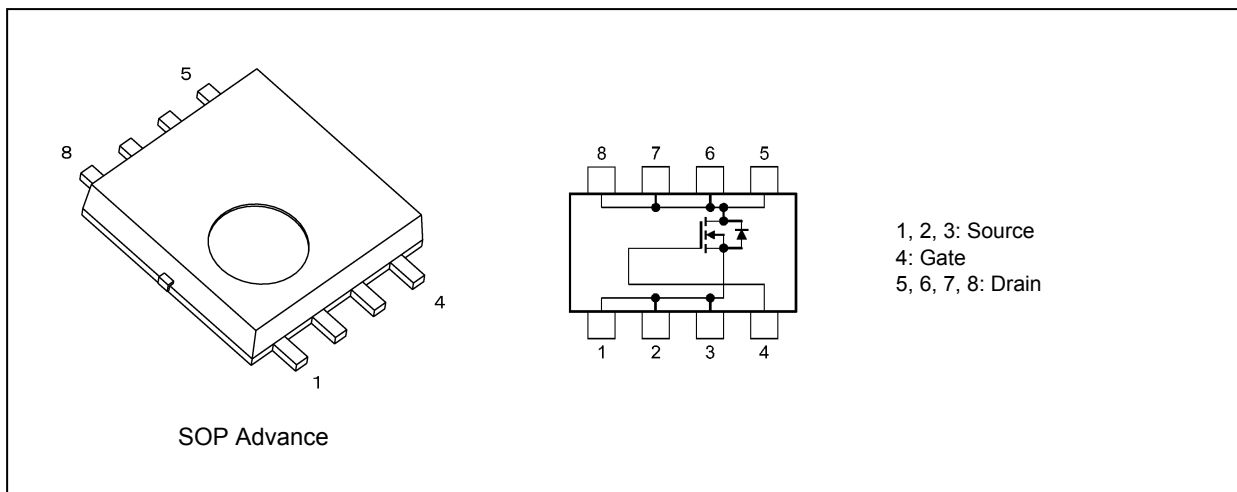
## 1. Applications

- High-Efficiency DC-DC Converters
- Notebook PCs
- Mobile Handsets

## 2. Features

- (1) Small, thin package
- (2) High-speed switching
- (3) Small gate charge:  $Q_{SW} = 3.3 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 12 \text{ m}\Omega \text{ (typ.) (} V_{GS} = 4.5 \text{ V)}$
- (5) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A (max) (} V_{DS} = 30 \text{ V)}$
- (6) Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V (} V_{DS} = 10 \text{ V, } I_D = 0.1 \text{ mA)}$

## 3. Packaging and Internal Circuit



**4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                                | Symbol    | Rating     | Unit             |
|--|-----------|------------|------------------|
| Drain-source voltage                           | $V_{DSS}$ | 30         | V                |
| Gate-source voltage                            | $V_{GSS}$ | $\pm 20$   |                  |
| Drain current (DC) (Note 1)                    | $I_D$     | 15         | A                |
| Drain current (pulsed) (Note 1)                | $I_{DP}$  | 45         |                  |
| Power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$     | 21         | W                |
| Power dissipation ( $t = 10$ s) (Note 2)       | $P_D$     | 2.8        | W                |
| Power dissipation ( $t = 10$ s) (Note 3)       | $P_D$     | 1.6        | W                |
| Single-pulse avalanche energy (Note 4)         | $E_{AS}$  | 58         | mJ               |
| Avalanche current                              | $I_{AR}$  | 15         | A                |
| Channel temperature                            | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature                            | $T_{stg}$ | -55 to 150 |                  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

**5. Thermal Characteristics**

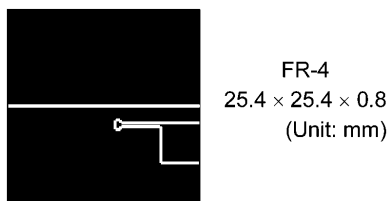
| Characteristics   | Symbol         | Max  | Unit               |
|---|----------------|------|--------------------|
| Channel-to-case thermal resistance ( $T_c = 25^\circ\text{C}$ ) | $R_{th(ch-c)}$ | 5.95 | $^\circ\text{C/W}$ |
| Channel-to-ambient thermal resistance ( $t = 10$ s) (Note 2)    | $R_{th(ch-a)}$ | 44.6 | $^\circ\text{C/W}$ |
| Channel-to-ambient thermal resistance ( $t = 10$ s) (Note 3)    | $R_{th(ch-a)}$ | 78.1 | $^\circ\text{C/W}$ |

Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

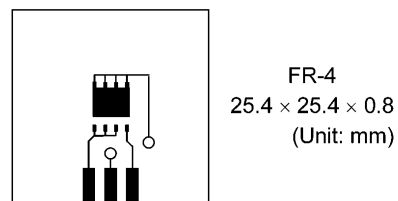
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{DD} = 24$  V,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.2$  mH,  $R_G = 1.2 \Omega$ ,  $I_{AR} = 15$  A



**Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)**



**Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)**

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

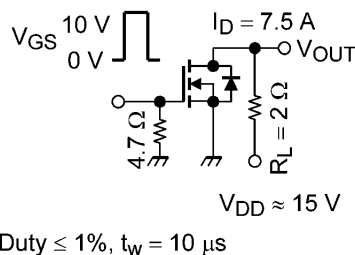
**6. Electrical Characteristics**

**6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol        | Test Condition                                  | Min | Typ. | Max       | Unit             |
|--------------------------------|---------------|---|-----|------|-----------|------------------|
| Gate leakage current           | $I_{GSS}$     | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | —   | —    | $\pm 0.1$ | $\mu\text{A}$    |
| Drain cut-off current          | $I_{DSS}$     | $V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$     | —   | —    | 10        |                  |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$       | 30  | —    | —         | V                |
|                                | $V_{(BR)DSX}$ | $I_D = 10\text{ mA}, V_{GS} = -20\text{ V}$     | 15  | —    | —         |                  |
| Gate threshold voltage         | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 0.1\text{ mA}$     | 1.3 | —    | 2.3       |                  |
| Drain-source on-resistance     | $R_{DS(ON)}$  | $V_{GS} = 4.5\text{ V}, I_D = 7.5\text{ A}$     | —   | 12   | 16        | $\text{m}\Omega$ |
|                                |               | $V_{GS} = 10\text{ V}, I_D = 7.5\text{ A}$      | —   | 9.3  | 11.6      |                  |

**6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol     | Test Condition  | Min | Typ. | Max  | Unit        |
|--------------------------------|------------|---|-----|------|------|-------------|
| Input capacitance              | $C_{iss}$  | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | —   | 980  | 1200 | $\text{pF}$ |
| Reverse transfer capacitance   | $C_{riss}$ |   | —   | 57   | 87   |             |
| Output capacitance             | $C_{oss}$  |   | —   | 210  | —    |             |
| Gate resistance                | $r_g$      | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 5\text{ MHz}$ | —   | 3.2  | 4.8  | $\Omega$    |
| Switching time (rise time)     | $t_r$      | See Figure 6.2.1.   | —   | 3.7  | —    | ns          |
| Switching time (turn-on time)  | $t_{on}$   |   | —   | 10   | —    |             |
| Switching time (fall time)     | $t_f$      |   | —   | 5.0  | —    |             |
| Switching time (turn-off time) | $t_{off}$  |   | —   | 24   | —    |             |



**Fig. 6.2.1 Switching Time Test Circuit**

**6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                                 | Symbol    | Test Condition  | Min | Typ. | Max | Unit |
|---|-----------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$ | —   | 14   | —   | nC   |
|   |           | $V_{DD} \approx 24\text{ V}, V_{GS} = 5\text{ V}, I_D = 15\text{ A}$  | —   | 7.2  | —   |      |
| Gate-source charge 1                            | $Q_{gs1}$ | $V_{DD} \approx 24\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$ | —   | 3.0  | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |   | —   | 1.8  | —   |      |
| Gate switch charge                              | $Q_{sw}$  |   | —   | 3.3  | —   |      |

**6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                         | Symbol    | Test Condition                              | Min | Typ. | Max  | Unit |
|---|-----------|---|-----|------|------|------|
| Reverse drain current (pulsed) (Note 5) | $I_{DRP}$ | —   | —   | —    | 45   | A    |
| Diode forward voltage                   | $V_{DSF}$ | $I_{DR} = 15\text{ A}, V_{GS} = 0\text{ V}$ | —   | —    | -1.2 | V    |

Note 5: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

7. Marking

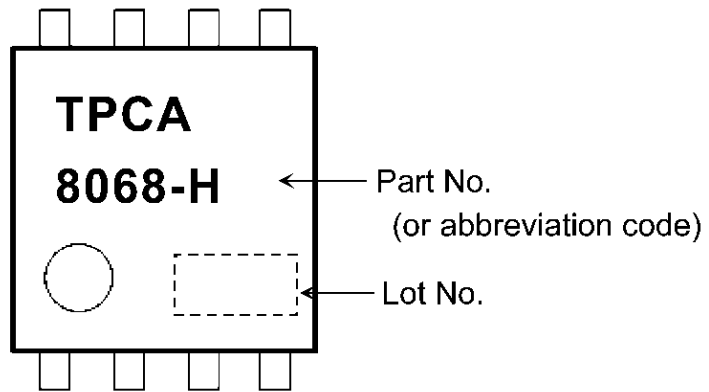
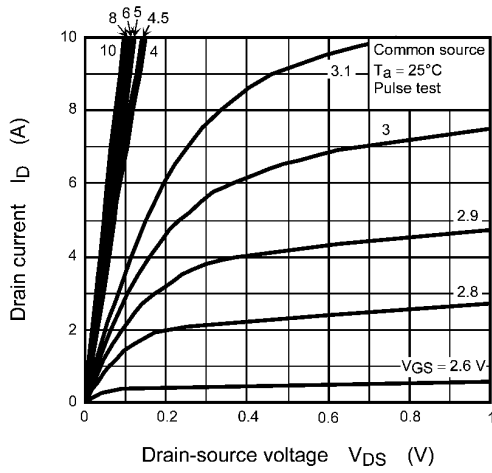
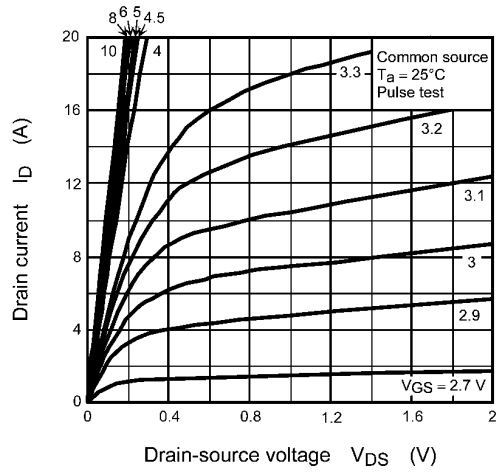


Fig. 7.1 Marking

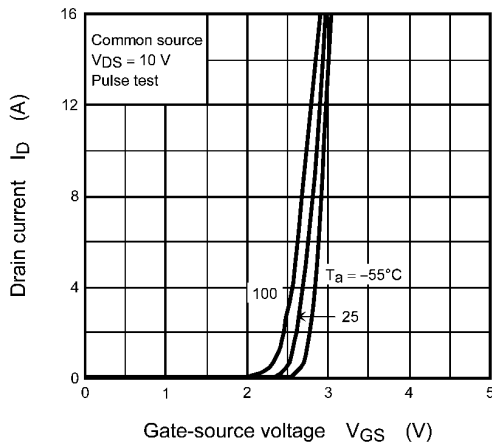
**8. Characteristics Curves (Note)**



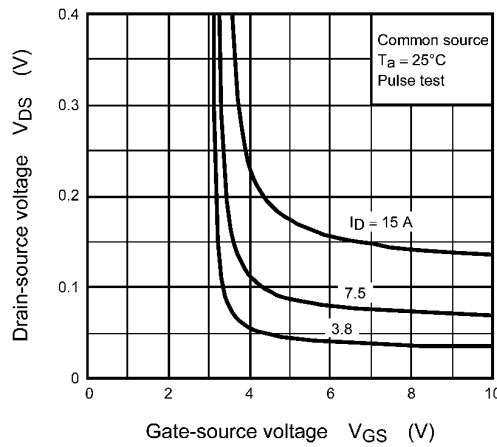
**Fig. 8.1  $I_D - V_{DS}$**



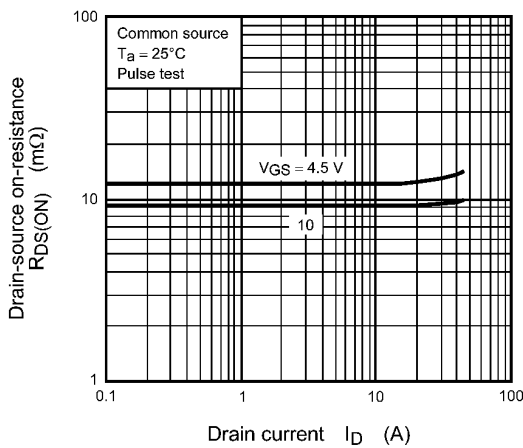
**Fig. 8.2  $I_D - V_{DS}$**



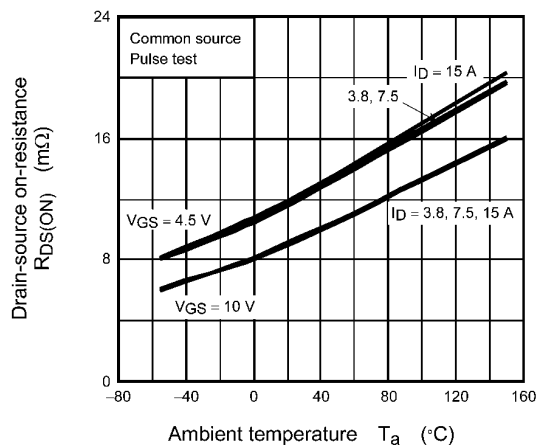
**Fig. 8.3  $I_D - V_{GS}$**



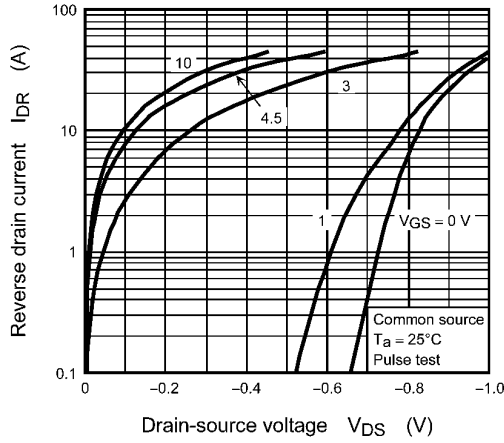
**Fig. 8.4  $V_{DS} - V_{GS}$**



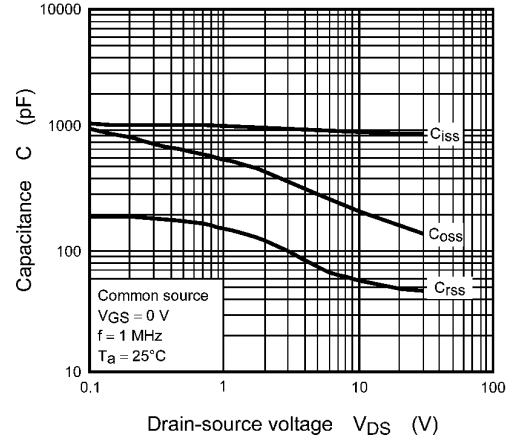
**Fig. 8.5  $R_{DS(ON)} - I_D$**



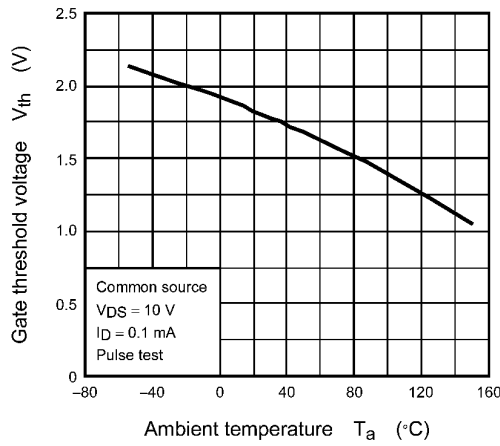
**Fig. 8.6  $R_{DS(ON)} - T_a$**



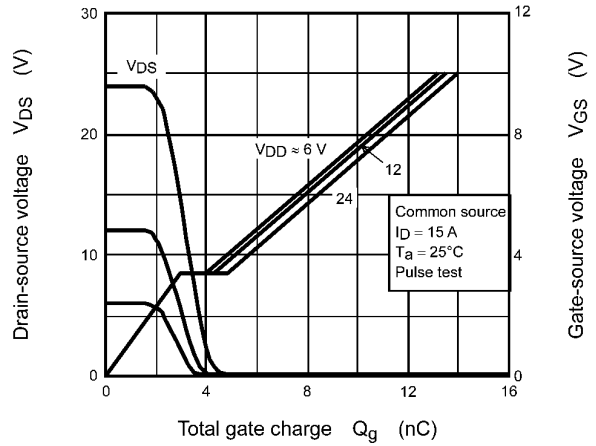
**Fig. 8.7  $I_{DR} - V_{DS}$**



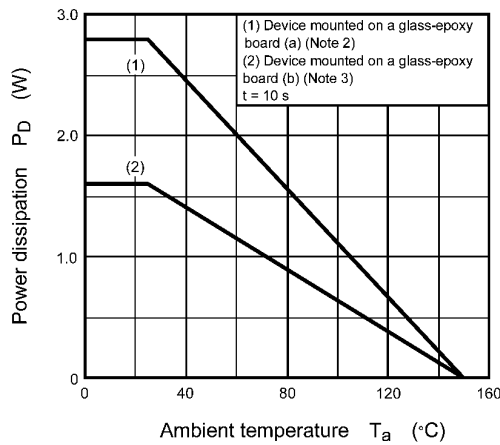
**Fig. 8.8 Capacitance -  $V_{DS}$**



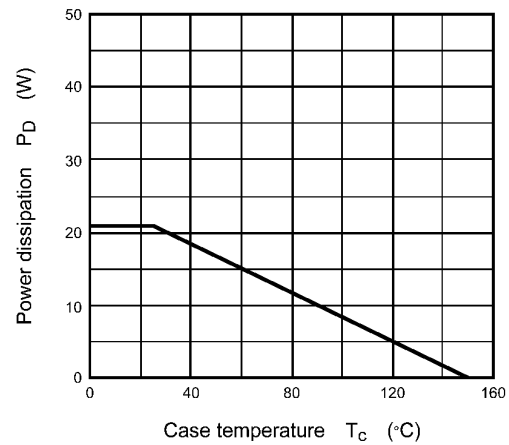
**Fig. 8.9  $V_{th} - T_A$**



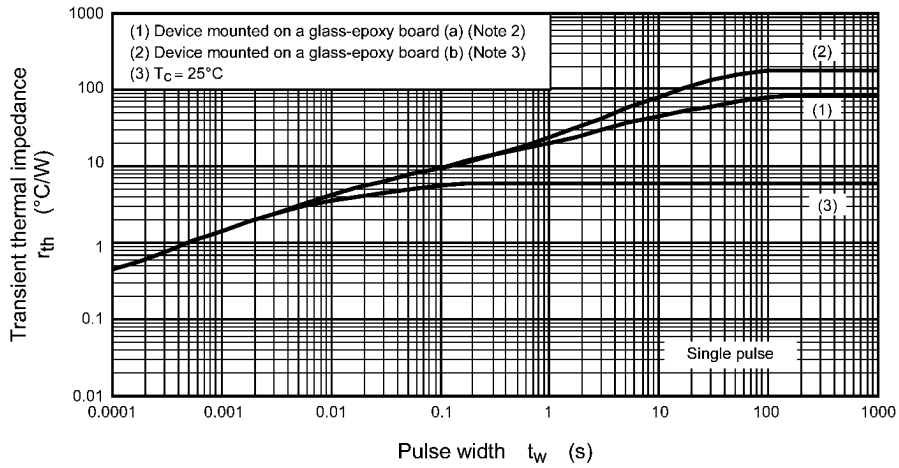
**Fig. 8.10 Dynamic Input/Output Characteristics**



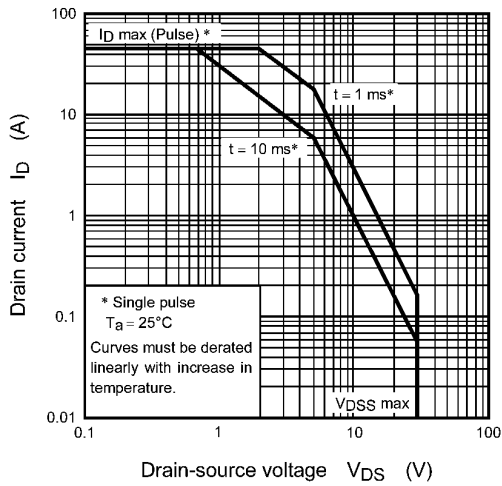
**Fig. 8.11  $P_D - T_A$   
(Guaranteed Maximum)**



**Fig. 8.12  $P_D - T_C$   
(Guaranteed Maximum)**



**Fig. 8.13  $r_{th} - t_w$**   
**(Guaranteed Maximum)**



**Fig. 8.14 Safe Operating Area**  
**(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.





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